

## MEASURING THE TIME SPENT TRAPDURING THE BARRIER-PARTE TUNNELING

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We present the principle behind an experiment that will measure the time spent traversing the potential barrier during a tunneling event. This experiment is accomplished by measuring the microscopically quantum tunneling current of the one electron gate of a current-biased Josephson junction connected to a transmission line of superconductor length. The transmission line provides a charge-dependent delay that reduces the tunneling rate. As the length of the line is increased from zero, the dependence of the tunneling rate changes from that corresponding to the transmission current to that corresponding to a constant equal to the line impedance. This constant value is the time delay time spent by the electron traversing the barrier.

Although quantum tunneling has been observed for many years, there exists a fundamental time scale [1,2] for this phenomenon that has not yet been directly measured. This time scale, called by Büttiker and Landauer [3] the "interval time for tunneling", is the time spent traversing the potential barrier during the tunneling event. In this paper we describe the theory that is the basis of an experiment, currently in progress at Orsay, in which we will measure this time.

The experiment is an outgrowth of recent theoretical understanding of low dissipation off-axis quantum tunneling [4]. The experimental system in which the measurement is being performed is the current-biased Josephson junction. This system is ideal because dissipation can be varied and controlled readily with all of the experimental parameters measured in situ [4].

The schematic representation of the system is given in fig. 1. A Josephson junction, of critical current  $I_c$  and capacitance  $C$ , is connected to a current bias  $I$  through a transmission line that is terminated by a resistor  $Z_0$ . The characteristic impedance of the line is  $Z_0$ , its length is  $l$ , and the propagation velocity is  $v$ . This system can be represented [4] by a particle of coordinate  $x$  moving in a tilted cosine potential  $V(x) = \Phi_0^2/2\pi g [I_c \cos(\pi x) - I]$ , where  $g$  is the superconductor phase difference across the junction, and  $\Phi_0 = hc/2e$ . The zero voltage state of the

junction corresponds to the particle residing in a local minimum of the potential. When the particle escapes, it continues moving along the potential; this corresponds to the voltage state of the junction. The experiments are usually conducted with  $l$ , slightly less than  $\lambda$ . In this case the potential is very well approximated by the vicinity of one of its local minima by a cubic potential, with barrier height  $\Delta V = (2\pi^2/3) I_c \Phi_0^2 / \lambda^2 - I \lambda_0^2 / 2$ . When the transmission line length  $l \rightarrow 0$ , the plasma oscillation frequency of the bottom of the well is  $\omega_0 = (2\pi C_0 / \Phi_0^2)^{1/2} [I - (I_c \lambda_0)^2]^{1/2}$ , of order a few GHz in our experiment.

We are interested in the escape of  $k$  from the metastable state. At temperature  $T=0$ , this escape occurs via macroscopic quantum tunneling [5]. For the case of no dissipation ( $Q \rightarrow \infty$ ) and  $Z_0 \rightarrow \infty$ , a WKB calculation predicts for the exponential part of the tunneling rate  $\Gamma^0 \propto \exp(-3.28/3k_0 \lambda)$ . The prediction for the case of a resistor shunting the junction ( $Q=0$ ) was given by Caldeira and Leggett [6]. When the dissipation is small ( $Q \rightarrow 0$  and  $Z_0$  large), the tunneling rate is given by  $\Gamma^0 \propto \exp(-3.28 g^2 / 3k_0 \lambda_0^2) + 0.85/Q + \dots$ , where  $Q = \pi v C_0 Z_0$ . Here we see that dissipation can strongly depress quantum tunneling.

For the case of a transmission line shunting the junction, we need Leggett's theory of quantum tunneling which takes into account frequency-dependent dissipation [7]. Using his work, one



Fig. 1. Schematic representation of a tunneling event through a junction connected to a transmission line of arbitrary length.

can then solve directly for the change in the tunneling exponent in perturbation theory for the case of small dissipation [5]. The result is:

$$F = \exp[-T_0(\Delta E)^2 \hbar \omega_p R] + \Delta E + \dots (1)$$

$$\Delta E = \frac{15}{8\pi} \int_0^{\infty} \frac{\Gamma_1 - i\omega \Gamma_2}{\sinh^2(\pi \hbar \omega / \omega_p)} d\omega,$$

and where  $\Gamma_1 - i\omega \Gamma_2$  is the external admittance loading the junction at negative imaginary frequencies. For the transmission line, the admittance is easily calculated to be

$$\Gamma(\omega) = \frac{1}{Z_0} \frac{Z_0 + iZ_0 \tan(\omega l)}{Z_0 + iZ_0 \tan(\omega l)},$$

Note that the admittance oscillates as a function of  $\omega$  at real frequencies, but becomes an exponentially varying function at imaginary frequencies.

We plot in fig. 2 the change in the tunneling exponent  $\Delta E$  versus transmission line length for



Fig. 2. Plot of the change in the tunneling exponent  $\Delta E$  versus length  $l$  of the transmission line for  $Z_0 = Z_0/2$ . The quantum dot steps having a characteristic length scale  $l_0 = \pi \hbar \omega_p / \omega_p$ . The time scale measuring the tunnel is  $\tau_0 = \hbar / \omega_p$ .

$Z_0 = Z_0/2$ . At length  $l = 0$ , the junction is closed by the resistor  $Z_0$  and we recover the linear dissipation prediction  $\Delta E = 0.675 \omega_p Z_0 C$ . For line lengths longer than about half the wavelength of radiation at frequency  $\omega_p/2\pi$ ,  $\Delta E$  approaches the value  $\Delta E = 0.675 \omega_p Z_0 C$ . In this case the radiation in tunneling is equivalent to the situation when the junction is closed by a resistor equal to the characteristic impedance of the line [6, 7]. It is interesting to note that the same prediction for  $\Delta E$  is found at long transmission line lengths for any value of the termination resistance. For example, this is found even if the line is terminated with an open circuit  $Z_0 = \infty$ . Thus, a line of finite length can look like a resistor even though it produces no physical energy loss.

We conclude that for long lengths, the tunneling process is only affected by the transmission line, and does not "see" the end of the line at all. A physical explanation of this is simple. Let us consider the correlation time  $\tau_c$  of the quantum fluctuations associated with the traversal of the potential barrier. If the delay time of the transmission line, given by  $l/v = 2l/v_0$ , is shorter than  $\tau_c$ , then the quantum fluctuations associated with the tunneling event interfere with themselves via reflections from the terminating impedance, and thus the termination will affect the tunneling rate. But if the delay time of the line is very long, then a tunneling event can no longer interfere with itself from a reflection off the termination. Thus, by measuring the characteristic length  $l_0$  in which the tunneling rate starts to change with  $l$ , one can infer the time  $\tau_c = 2l_0/v = 2\pi \hbar / \omega_p$ .

The theoretical prediction for the change in the tunneling rate versus line length is directly related to the imaginary frequency dependence of the admittance. Thus, an observation of  $\omega_p$  steps (not without an oscillatory behavior) will be a confirmation of this imaginary frequency dependence, as predicted by Leggett's theory. In addition, the width and position of energy-level transitions [4] in the potential well are predicted to be proportional to real and imaginary parts of  $\Gamma(\omega)$  [6]. Since this depends on  $\Gamma(\omega)$  at real frequencies, this phenomenon will manifest as a function of  $l$ .

In our experiment, the junction films and measuring apparatus are similar to those described elsewhere [1]. The junction itself is of primary importance here, and is constructed as follows. The junction is positioned at one end of a coplanar transmission line of impedance  $50\Omega$ . A microwave termination resistor is made by plating a metal bar with a thin insulating coating over the transmission line. The metal bar provides a microwave short from ground to the junction resistance, thus reducing the line's characteristic impedance. A microwave absorbing material is also included in this metal bar to suppress standing wave resonances in the bar. The end of the bar facing the junction thus acts like a termination resistance with respect to microwave radiation originating from the junction and reflecting off the bar. The bar is moved while it is at low temperature ( $T \sim 20\text{mK}$ ) by a spring attached between it and the top of the dilution refrigerator cryostat. Thus, we are able to measure the change in the escape rate of the junction versus line length while keeping all of the junction parameters constant.

In a separate but related experiment, we have investigated the thermal escape rate versus line

length at liquid He temperatures. In this temperature regime the exponential factor of the escape rate prediction,  $\exp(-\Delta C^2/\mathcal{P})$ , is independent of  $l$ , and the escape rate changes only because the thermal prefactor changes. For low damped systems, theory predicts that the prefactor should oscillate with line length [2]. This effect has indeed been observed experimentally by our group.

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